

Vladimir Gavrilenko

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180
papers

1,676
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h-index

31
g-index

203
ext. papers

2,056
ext. citations

1.6
avg, IF

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L-index

#	Paper	IF	Citations
180	Observation of three-dimensional massless Kane fermions in a zinc-blende crystal. <i>Nature Physics</i> , 2014 , 10, 233-238	16.2	143
179	Temperature-driven massless Kane fermions in HgCdTe crystals. <i>Nature Communications</i> , 2016 , 7, 125761	17.4	47
178	Stimulated emission from HgCdTe quantum well heterostructures at wavelengths up to 19.5 μm . <i>Applied Physics Letters</i> , 2017 , 111, 192101	3.4	44
177	Effective third-order nonlinearities in metallic refractory titanium nitride thin films. <i>Optical Materials Express</i> , 2015 , 5, 2395	2.6	40
176	Cyclotron resonance in HgTe/CdTe-based heterostructures in high magnetic fields. <i>Nanoscale Research Letters</i> , 2012 , 7, 534	5	39
175	High-responsivity terahertz detection by on-chip InGaAs/GaAs field-effect-transistor array. <i>Applied Physics Letters</i> , 2011 , 98, 153504	3.4	38
174	Cyclotron resonance and interband optical transitions in HgTe/CdTe(0 1 3) quantum well heterostructures. <i>Semiconductor Science and Technology</i> , 2011 , 26, 125011	1.8	37
173	Pressure- and temperature-driven phase transitions in HgTe quantum wells. <i>Physical Review B</i> , 2016 , 94,	3.3	36
172	Experimental study of frequency multipliers based on a GaAs/AlAs semiconductor superlattices in the terahertz frequency range. <i>Semiconductors</i> , 2012 , 46, 121-125	0.7	35
171	HgCdTe-based heterostructures for terahertz photonics. <i>APL Materials</i> , 2017 , 5, 035503	5.7	33
170	Exchange enhancement of the g factor in InAs/AlSb heterostructures. <i>Semiconductors</i> , 2008 , 42, 828-833	0.7	31
169	Efficient long wavelength interband photoluminescence from HgCdTe epitaxial films at wavelengths up to 26 μm . <i>Applied Physics Letters</i> , 2014 , 104, 072102	3.4	28
168	Study of lifetimes and photoconductivity relaxation in heterostructures with Hg _x Cd _{1-x} Te/Cd _y Hg _{1-y} Te quantum wells. <i>Semiconductors</i> , 2012 , 46, 1362-1366	0.7	27
167	Long wavelength stimulated emission up to 9.5 μm from HgCdTe quantum well heterostructures. <i>Applied Physics Letters</i> , 2016 , 108, 092104	3.4	25
166	Terahertz spectroscopy of quantum-well narrow-bandgap HgTe/CdTe-based heterostructures. <i>JETP Letters</i> , 2010 , 92, 756-761	1.2	24
165	Anticrossing of Landau levels in HgTe/CdHgTe (013) quantum wells with an inverted band structure. <i>JETP Letters</i> , 2015 , 100, 790-794	1.2	23
164	Time resolved photoluminescence spectroscopy of narrow gap Hg _{1-x} Cd _x Te/Cd _y Hg _{1-y} Te quantum well heterostructures. <i>Applied Physics Letters</i> , 2014 , 105, 022102	3.4	23

163	Temperature-driven single-valley Dirac fermions in HgTe quantum wells. <i>Physical Review B</i> , 2017 , 96,	3.3	23
162	Persistent photoconductivity in InAs/AlSb heterostructures with double quantum wells. <i>Semiconductors</i> , 2010 , 44, 616-622	0.7	23
161	Spectra and kinetics of THz photoconductivity in narrow-gap Hg _{1-x} CdxTe (<i>Semiconductor Science and Technology</i> , 2013 , 28, 125007	1.8	21
160	Impurity breakdown and terahertz luminescence in n-GaN epilayers under external electric field. <i>Journal of Applied Physics</i> , 2009 , 106, 123523	2.5	21
159	Electron transport and detection of terahertz radiation in a GaN/AlGaIn submicrometer field-effect transistor. <i>Semiconductors</i> , 2007 , 41, 232-234	0.7	21
158	Electron-electron interaction and spin-orbit coupling in InAs/AlSb heterostructures with a two-dimensional electron gas. <i>Semiconductors</i> , 2011 , 45, 110-117	0.7	20
157	Spin splitting in HgTe/CdHgTe (013) quantum well heterostructures. <i>JETP Letters</i> , 2010 , 92, 63-66	1.2	20
156	GaAsSb/GaAs strained structures with quantum wells for lasers with emission wavelength near 1.3 μm . <i>Semiconductors</i> , 2010 , 44, 405-412	0.7	19
155	Electron transport and terahertz radiation detection in submicrometer-sized GaAs/AlGaAs field-effect transistors with two-dimensional electron gas. <i>Physics of the Solid State</i> , 2004 , 46, 146-149	0.8	19
154	Shallow acceptors in strained Ge/Ge _{1-x} Si _x heterostructures with quantum wells. <i>Semiconductors</i> , 2000 , 34, 563-567	0.7	19
153	Terahertz radiation generation in multilayer quantum-cascade heterostructures. <i>Technical Physics Letters</i> , 2017 , 43, 362-365	0.7	18
152	Temperature-dependent magnetospectroscopy of HgTe quantum wells. <i>Physical Review B</i> , 2016 , 94,	3.3	18
151	Stimulated emission in the 2.8-3.5 μm wavelength range from Peltier cooled HgTe/CdHgTe quantum well heterostructures. <i>Optics Express</i> , 2018 , 26, 12755-12760	3.3	18
150	Rashba spin splitting and exchange enhancement of the g factor in InAs/AlSb heterostructures with a two-dimensional electron gas. <i>Semiconductors</i> , 2012 , 46, 1163-1170	0.7	18
149	High performance single emitter homojunction interfacial work function far infrared detectors. <i>Journal of Applied Physics</i> , 2004 , 95, 512-519	2.5	18
148	Terahertz photoconductivity of double acceptors in narrow gap HgCdTe epitaxial films grown by molecular beam epitaxy on GaAs(013) and Si(013) substrates. <i>Semiconductor Science and Technology</i> , 2017 , 32, 095007	1.8	17
147	Features of the persistent photoconductivity in InAs/AlSb heterostructures with double quantum wells and a tunneling-transparent barrier. <i>Semiconductors</i> , 2012 , 46, 1396-1401	0.7	17
146	Theory of g-factor enhancement in narrow-gap quantum well heterostructures. <i>Journal of Physics Condensed Matter</i> , 2011 , 23, 385601	1.8	17

145	Room-temperature intracavity difference-frequency generation in butt-joint diode lasers. <i>Applied Physics Letters</i> , 2008 , 92, 021122	3.4	17
144	Effect of electron-electron interaction on cyclotron resonance in high-mobility InAs/AlSb quantum wells. <i>Journal of Applied Physics</i> , 2015 , 117, 112813	2.5	15
143	Specific features of the spectra and relaxation kinetics of long-wavelength photoconductivity in narrow-gap HgCdTe epitaxial films and heterostructures with quantum wells. <i>Semiconductors</i> , 2013 , 47, 1438-1441	0.7	15
142	Spectra of persistent photoconductivity in InAs/AlSb quantum-well heterostructures. <i>Semiconductors</i> , 2005 , 39, 22	0.7	15
141	Cyclotron resonance in doped and undoped InAs/AlSb heterostructures with quantum wells. <i>Semiconductors</i> , 2005 , 39, 62	0.7	15
140	Cyclotron resonance study in InAs/AlSb quantum well heterostructures with two occupied electronic subbands. <i>Journal of Applied Physics</i> , 2012 , 111, 093711	2.5	14
139	Spin-wave excitations and electron spin resonance in symmetric and asymmetric narrow-gap quantum wells. <i>Physical Review B</i> , 2013 , 87,	3.3	14
138	High-field splitting of the cyclotron resonance absorption in strained p-InGaAs/GaAs quantum wells. <i>Physical Review B</i> , 2009 , 79,	3.3	14
137	Long-wavelength injection lasers based on Pb _{1-x} Sn _x Se alloys and their use in solid-state spectroscopy. <i>Semiconductors</i> , 2015 , 49, 1623-1626	0.7	13
136	Type II to Type I conversion of GaAs/GaAsSb heterostructure energy spectrum under optical pumping. <i>Journal of Applied Physics</i> , 2013 , 113, 163107	2.5	13
135	Nonlinear mode mixing in dual-wavelength semiconductor lasers with tunnel junctions. <i>Applied Physics Letters</i> , 2007 , 90, 171106	3.4	13
134	Fundamental Limits to Far-Infrared Lasing in Auger-Suppressed HgCdTe Quantum Wells. <i>ACS Photonics</i> , 2020 , 7, 98-104	6.3	13
133	Temperature-dependent terahertz spectroscopy of inverted-band three-layer InAs/GaSb/InAs quantum well. <i>Physical Review B</i> , 2018 , 97,	3.3	13
132	Features of impurity-photoconductivity relaxation in boron-doped silicon. <i>Semiconductors</i> , 2012 , 46, 1387-1391	0.7	12
131	Long wavelength superluminescence from narrow gap HgCdTe epilayer at 100 K. <i>Applied Physics Letters</i> , 2015 , 107, 042105	3.4	11
130	Cyclotron resonance in HgTe/CdTe(013) narrowband heterostructures in quantized magnetic fields. <i>JETP Letters</i> , 2012 , 95, 406-410	1.2	11
129	Carrier Recombination, Long-Wavelength Photoluminescence, and Stimulated Emission in HgCdTe Quantum Well Heterostructures. <i>Physica Status Solidi (B): Basic Research</i> , 2019 , 256, 1800546	1.3	10
128	Terahertz detection of magnetic field-driven topological phase transition in HgTe-based transistors. <i>Applied Physics Letters</i> , 2015 , 107, 152101	3.4	10

127	Cyclotron resonance quantum Hall effect detector. <i>Semiconductor Science and Technology</i> , 2001 , 16, 300-303	1.8	10
126	Landau level spectroscopy of valence bands in HgTe quantum wells: effects of symmetry lowering. <i>Journal of Physics Condensed Matter</i> , 2019 , 31, 145501	1.8	10
125	Radiative recombination in narrow gap HgTe/CdHgTe quantum well heterostructures for laser applications. <i>Journal of Physics Condensed Matter</i> , 2018 , 30, 495301	1.8	10
124	Magneto-transport in inverted HgTe quantum wells. <i>Npj Quantum Materials</i> , 2019 , 4,	5	9
123	Terahertz emission and photoconductivity in n-type GaAs/AlGaAs quantum wells: the role of resonant impurity states. <i>Semiconductors</i> , 2010 , 44, 1394-1397	0.7	9
122	Kinetics of terahertz photoconductivity in p-Ge under impurity breakdown conditions. <i>Semiconductors</i> , 2010 , 44, 1476-1479	0.7	9
121	Balance-equation method for simulating terahertz quantum-cascade lasers using a wave-function basis with reduced dipole moments of tunnel-coupled states. <i>Quantum Electronics</i> , 2019 , 49, 913-918	1.8	8
120	Magneto-spectroscopy of double HgTe/CdHgTe quantum wells. <i>Semiconductors</i> , 2016 , 50, 1532-1538	0.7	8
119	Wide-aperture detector of terahertz radiation based on GaAs/InGaAs transistor structure with large-area slit grating gate. <i>Technical Physics Letters</i> , 2010 , 36, 365-368	0.7	8
118	Shallow acceptors in Ge/GeSi strained multilayer heterostructures with quantum wells. <i>JETP Letters</i> , 1997 , 65, 209-214	1.2	8
117	Fano resonance study in impurity photocurrent spectra of bulk GaAs and GaAs quantum wells doped with shallow donors. <i>Physical Review B</i> , 2007 , 75,	3.3	8
116	Effect of magnetic field quantization on the shallow acceptor spectrum in strained Ge/GeSi heterostructures. <i>Physical Review B</i> , 2002 , 66,	3.3	8
115	Temperature limitations for stimulated emission in 3 μ m range due to threshold and non-threshold Auger recombination in HgTe/CdHgTe quantum wells. <i>Applied Physics Letters</i> , 2020 , 117, 083103	3.4	8
114	Terahertz imaging of Landau levels in HgTe-based topological insulators. <i>Applied Physics Letters</i> , 2016 , 108, 262102	3.4	8
113	Temperature Dependences of the Threshold Current and Output Power of a Quantum-Cascade Laser Emitting at 3.3 THz. <i>Semiconductors</i> , 2018 , 52, 1380-1385	0.7	8
112	Rashba spin splitting and cyclotron resonance in strained InGaAs/InP heterostructures with a two-dimensional electron gas. <i>Semiconductors</i> , 2013 , 47, 1485-1491	0.7	7
111	Exchange interaction effects in electron spin resonance: Larmor theorem violation in narrow-gap quantum well heterostructures. <i>Journal of Physics Condensed Matter</i> , 2012 , 24, 252201	1.8	7
110	The effect of exchange interaction on quasiparticle Landau levels in narrow-gap quantum well heterostructures. <i>Journal of Physics Condensed Matter</i> , 2012 , 24, 135601	1.8	7

109	Long-wavelength stimulated emission and carrier lifetimes in HgCdTe-based waveguide structures with quantum wells. <i>Semiconductors</i> , 2016 , 50, 1651-1656	0.7	7
108	Terahertz Injection Lasers Based on a PbSnSe Solid Solution with an Emission Wavelength up to 50 μm and Their Application in the Magnetospectroscopy of Semiconductors. <i>Semiconductors</i> , 2018 , 52, 1590-1594	0.7	7
107	Massless Dirac fermions in III-V semiconductor quantum wells. <i>Physical Review B</i> , 2019 , 99,	3.3	6
106	Terahertz injection lasers based on PbSnSe alloy with an emission wavelength up to 46.5 μm . <i>Semiconductors</i> , 2016 , 50, 1669-1672	0.7	6
105	Features of Photoluminescence of Double Acceptors in HgTe/CdHgTe Heterostructures with Quantum Wells in a Terahertz Range. <i>JETP Letters</i> , 2019 , 109, 657-662	1.2	6
104	Investigation of HgCdTe waveguide structures with quantum wells for long-wavelength stimulated emission. <i>Semiconductors</i> , 2017 , 51, 1557-1561	0.7	6
103	Impurity-induced photoconductivity of narrow-gap CadmiumMercuryTelluride structures. <i>Semiconductors</i> , 2015 , 49, 1605-1610	0.7	6
102	Detection of terahertz radiation by tightly concatenated InGaAs field-effect transistors integrated on a single chip. <i>Applied Physics Letters</i> , 2014 , 104, 163508	3.4	6
101	The cyclotron resonance of holes in InGaAs/GaAs heterostructures with quantum wells in quantizing magnetic fields. <i>Semiconductors</i> , 2010 , 44, 1492-1494	0.7	6
100	Infrared magneto-spectroscopy of two-dimensional and three-dimensional massless fermions: A comparison. <i>Journal of Applied Physics</i> , 2015 , 117, 112803	2.5	5
99	Exchange enhancement of the electron g-factor in a two-dimensional semimetal in HgTe quantum wells. <i>Semiconductors</i> , 2015 , 49, 1627-1633	0.7	5
98	Magnetoabsorption in narrow-gap HgCdTe epitaxial layers in the terahertz range. <i>Semiconductors</i> , 2013 , 47, 1545-1550	0.7	5
97	On the band spectrum in p-type HgTe/CdHgTe heterostructures and its transformation under temperature variation. <i>Semiconductors</i> , 2017 , 51, 1531-1536	0.7	5
96	Investigation of magnetoabsorption at different temperatures in HgTe/CdHgTe quantum-well heterostructures in pulsed magnetic fields. <i>Semiconductors</i> , 2015 , 49, 1611-1615	0.7	5
95	Resonant states of shallow acceptors in uniaxially deformed germanium. <i>Journal of Experimental and Theoretical Physics</i> , 2001 , 93, 1296-1301	1	5
94	Infrared radiation from hot holes during spatial transport in selectively doped InGaAs/GaAs heterostructures with quantum wells. <i>JETP Letters</i> , 1996 , 64, 520-524	1.2	5
93	Mercury vacancies as divalent acceptors in $\text{Hg}_y\text{Te}_{1-y}/\text{Cd}_x\text{Hg}_{1-x}\text{Te}$ structures with quantum wells. <i>Semiconductors</i> , 2016 , 50, 1662-1668	0.7	5
92	Bipolar Persistent Photoconductivity in HgTe/CdHgTe (013) Double Quantum-Well Heterostructures. <i>Semiconductors</i> , 2018 , 52, 1586-1589	0.7	5

91	Second-Harmonic Generation of Subterahertz Gyrotron Radiation by Frequency Doubling in InP:Fe and Its Application for Magnetospectroscopy of Semiconductor Structures. <i>Semiconductors</i> , 2019 , 53, 1217-1221	0.7	4
90	Study of the Auger Recombination Energy Threshold in a Series of Waveguide Heterostructures with HgTe/Cd _{0.7} Hg _{0.3} Te QWs Near 14 μ m. <i>Semiconductors</i> , 2019 , 53, 1154-1157	0.7	4
89	Exchange enhancement of the electron g factor in strained InGaAs/InP heterostructures. <i>Semiconductors</i> , 2015 , 49, 191-198	0.7	4
88	Effect of the direct capture of holes with the emission of optical phonons on impurity-photoconductivity relaxation in p-Si:B. <i>Semiconductors</i> , 2015 , 49, 187-190	0.7	4
87	Chain of Dirac spectrum loops of nodes in crossed magnetic and electric fields. <i>Physical Review B</i> , 2018 , 97,	3.3	4
86	Detection of Terahertz Radiation by Dense Arrays of InGaAs Transistors. <i>International Journal of High Speed Electronics and Systems</i> , 2015 , 24, 1550002	0.5	4
85	Studying the frequency tuning of pulsed terahertz quantum cascade lasers. <i>Radiophysics and Quantum Electronics</i> , 2012 , 54, 609-615	0.7	4
84	Difference-frequency generation in a butt-join diode laser. <i>Semiconductors</i> , 2009 , 43, 208-211	0.7	4
83	Relaxation of the impurity photoconductivity in p-Ge/Ge _{1-x} Si _x quantum well heterostructures. <i>Semiconductor Science and Technology</i> , 2011 , 26, 085009	1.8	4
82	Cyclotron Resonance of Extremely Conductive 2D Holes in High Ge Content Strained Heterostructures. <i>Journal of Low Temperature Physics</i> , 2010 , 159, 216-221	1.3	4
81	A multifrequency interband two-cascade laser. <i>Semiconductors</i> , 2007 , 41, 1209-1213	0.7	4
80	On the impurity photoconductivity of uniaxially stressed p-Ge. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003 , 680-682		4
79	Current oscillations under lateral transport in GaAs/InGaAs quantum well heterostructures. <i>Semiconductors</i> , 2005 , 39, 44	0.7	4
78	Sub-terahertz FET detector with self-assembled Sn-nanowires. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 075102	3	4
77	Auger recombination in narrow gap HgCdTe/CdHgTe quantum well heterostructures. <i>Journal of Applied Physics</i> , 2021 , 129, 133106	2.5	4
76	Terahertz Photoluminescence of Double Acceptors in Bulky Epitaxial HgCdTe Layers and HgTe/CdHgTe Structures with Quantum Wells. <i>Journal of Experimental and Theoretical Physics</i> , 2018 , 127, 1125-1129	1	4
75	Effect of Features of the Band Spectrum on the Characteristics of Stimulated Emission in Narrow-Gap Heterostructures with HgCdTe Quantum Wells. <i>Semiconductors</i> , 2018 , 52, 1375-1379	0.7	4
74	Calculation of Multiply Charged States of Impurity-Defect Centers in Epitaxial Hg _{1-x} Cd _x Te Layers. <i>Semiconductors</i> , 2018 , 52, 1369-1374	0.7	4

73	Cyclotron resonance of dirac fermions in InAs/GaSb/InAs quantum wells. <i>Semiconductors</i> , 2017 , 51, 38-42.	0.7	3
72	Relaxation kinetics of impurity photoconductivity in p-Si:B with various levels of doping and degrees of compensation in high electric fields. <i>Semiconductors</i> , 2013 , 47, 1461-1464	0.7	3
71	Magnetoabsorption of Dirac Fermions in InAs/GaSb/InAs Three-Layer Gapless Quantum Wells. <i>JETP Letters</i> , 2017 , 106, 727-732	1.2	3
70	Investigation of possibility of VLWIR lasing in HgCdTe based heterostructures. <i>Journal of Physics: Conference Series</i> , 2015 , 647, 012008	0.3	3
69	Determination of the heterojunction type in structures with GaAsSb/GaAs quantum wells with various antimony fractions by optical methods. <i>Semiconductors</i> , 2012 , 46, 1376-1380	0.7	3
68	Fano resonances in the impurity photocurrent spectra of GaAs samples and an InGaAs/GaAsP quantum-well heterostructure doped with shallow acceptors. <i>Journal of Experimental and Theoretical Physics</i> , 2009 , 109, 466-471	1	3
67	High-resolution emission spectra of pulsed terahertz quantum-cascade lasers. <i>Semiconductors</i> , 2010 , 44, 1467-1471	0.7	3
66	Far Infrared Emission and Absorption (Amplification) under Real Space Transfer and Population Inversion in Shallow Multi-Quantum-Wells. <i>Physica Status Solidi (B): Basic Research</i> , 1997 , 204, 563-565	1.3	3
65	Fano resonance in the impurity photoconductivity spectrum of InP doped with shallow donors. <i>Physics of the Solid State</i> , 2008 , 50, 1211-1214	0.8	3
64	Fano resonances in the impurity photoexcitation spectra of semiconductors doped with shallow donors. <i>Journal of Experimental and Theoretical Physics</i> , 2005 , 101, 708-716	1	3
63	Time constant of the far-IR response of a quantum Hall device. <i>Nanotechnology</i> , 2001 , 12, 453-456	3.4	3
62	Plasmon recombination in narrowgap HgTe quantum wells. <i>Journal of Physics Communications</i> , 2020 , 4, 115012	1.2	3
61	Calculation of Wave Functions of Resonant Acceptor States in Narrow-Gap CdHgTe Compounds. <i>Semiconductors</i> , 2020 , 54, 827-831	0.7	3
60	Magnetoconductivity and Terahertz Response of a HgCdTe Epitaxial Layer. <i>Sensors</i> , 2018 , 18,	3.8	3
59	Experimental Observation of Temperature-Driven Topological Phase Transition in HgTe/CdHgTe Quantum Wells. <i>Condensed Matter</i> , 2019 , 4, 27	1.8	2
58	Terahertz Emission from HgCdTe QWs under Long-Wavelength Optical Pumping. <i>Journal of Infrared, Millimeter, and Terahertz Waves</i> , 2020 , 41, 750-757	2.2	2
57	Terahertz emission from CdHgTe/HgTe quantum wells with an inverted band structure. <i>Semiconductors</i> , 2016 , 50, 915-919	0.7	2
56	Residual-Photoconductivity Spectra in HgTe/CdHgTe Quantum-Well Heterostructures. <i>Semiconductors</i> , 2019 , 53, 1363-1366	0.7	2

55	Diagnostics of quantum cascade structures by optical methods in the near infrared region. <i>Semiconductors</i> , 2012 , 46, 1411-1414	0.7	2
54	Emission spectra of terahertz quantum cascade laser. <i>Radiophysics and Quantum Electronics</i> , 2009 , 52, 494-499	0.7	2
53	Resonance detection of terahertz radiation in submicrometer field-effect GaAs/AlGaAs transistors with two-dimensional electron gas. <i>Semiconductors</i> , 2009 , 43, 528-531	0.7	2
52	Shallow-impurity-assisted transitions in the course of submillimeter magnetoabsorption of strained Ge/GeSi(111) quantum-well heterostructures. <i>Physics of the Solid State</i> , 2004 , 46, 125-129	0.8	2
51	Intersubband cyclotron resonance of holes in strained Ge/GeSi(111) heterostructures with germanium wide quantum wells and cyclotron resonance of 1L electrons in GeSi layers. <i>Physics of the Solid State</i> , 2004 , 46, 130-137	0.8	2
50	Specific Growth Features of Nanostructures for Terahertz Quantum Cascade Lasers and Their Physical Properties. <i>Semiconductors</i> , 2020 , 54, 1092-1095	0.7	2
49	Mid-infrared stimulated emission in HgCdTe/CdHgTe quantum well heterostructures at room temperature. <i>Optical Engineering</i> , 2020 , 60,	1.1	2
48	Mid-IR stimulated emission in Hg(Cd)Te/CdHgTe quantum well structures up to 200 K due to suppressed Auger recombination. <i>Laser Physics</i> , 2021 , 31, 015801	1.2	2
47	Probing States of a Double Acceptor in CdHgTe Heterostructures via Optical Gating. <i>JETP Letters</i> , 2020 , 111, 575-581	1.2	2
46	Observation of topological phase transition by terahertz photoconductivity in HgTe-based transistors. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2016 , 13, 534-537		2
45	Feasibility of lasing in the GaAs Reststrahlen band with HgTe multiple quantum well laser diodes. <i>Journal Physics D: Applied Physics</i> , 2021 , 54, 175108	3	2
44	Polarization-Sensitive Fourier-Transform Spectroscopy of HgTe/CdHgTe Quantum Wells in the Far Infrared Range in a Magnetic Field. <i>JETP Letters</i> , 2018 , 108, 329-334	1.2	2
43	Evolution of the Impurity Photoconductivity in CdHgTe Epitaxial Films with Temperature. <i>Semiconductors</i> , 2019 , 53, 1266-1271	0.7	1
42	Magnetoabsorption in HgCdTe/CdHgTe Quantum Wells in Tilted Magnetic Fields. <i>JETP Letters</i> , 2019 , 109, 191-197	1.2	1
41	Cyclotron resonance in HgCdTe-based heterostructures in strong magnetic fields. <i>Journal of Physics: Conference Series</i> , 2013 , 461, 012038	0.3	1
40	Effects of Rashba spin splitting and exchange interaction in electron spin resonance in narrow-gap quantum well heterostructures. <i>Journal of Physics: Conference Series</i> , 2013 , 456, 012021	0.3	1
39	Shallow acceptors in strained multiquantum-well Ge/Ge _{1-x} Si _x heterostructures. <i>Semiconductors</i> , 1998 , 32, 1106-1110	0.7	1
38	Magnetic field dependence of the photoresponse time of GaAs/AlGaAs quantum Hall effect device. <i>Semiconductor Science and Technology</i> , 2008 , 23, 095014	1.8	1

37	Experimental study of nonlinear mode mixing in dual-wavelength semiconductor lasers. <i>Laser Physics</i> , 2007 , 17, 684-687	1.2	1
36	Frequency shift in a system of two laser diodes. <i>Semiconductors</i> , 2007 , 41, 1364-1368	0.7	1
35	Negative photoconductivity of selectively doped SiGe/Si: B heterostructures with a two-dimensional hole gas in the middle-infrared range. <i>Physics of the Solid State</i> , 2005 , 47, 46	0.8	1
34	Toward Peltier-cooled mid-infrared HgCdTe lasers: Analyzing the temperature quenching of stimulated emission at ~6 μ m wavelength from HgCdTe quantum wells. <i>Journal of Applied Physics</i> , 2021 , 130, 214302	2.5	1
33	Continuous-Wave Stimulated Emission in the 10 μ m-14 μ m Range under Optical Excitation in HgCdTe/CdHgTe-QW Structures with Quasirelativistic Dispersion. <i>Semiconductors</i> , 2020 , 54, 1371-1375	0.7	1
32	Express Characterization of the HgCdTe/CdHgTe Quantum Well Waveguide Heterostructures with the Quasi-Relativistic Carrier Dispersion Law by Room-Temperature Photoluminescence Spectroscopy. <i>Technical Physics Letters</i> , 2021 , 47, 154-157	0.7	1
31	Terahertz Spectroscopy of Two-Dimensional Semimetal in Three-Layer InAs/GaSb/InAs Quantum Well. <i>JETP Letters</i> , 2019 , 109, 96-101	1.2	0
30	Detection of Terahertz Radiation by Dense Arrays of InGaAs Transistors. <i>Selected Topics in Electronics and Systems</i> , 2015 , 31-53	0	0
29	Effects of the Electron-Electron Interaction in the Magneto-Absorption Spectra of HgTe/CdHgTe Quantum Wells with an Inverted Band Structure. <i>JETP Letters</i> , 2020 , 112, 508-512	1.2	0
28	Investigation of the Photosensitivity of Narrow-Gap and Gapless HgCdTe Solid Solutions in the Terahertz and Sub-Terahertz Range. <i>Semiconductors</i> , 2020 , 54, 1096-1102	0.7	0
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26	Magneto-optics of HgTe/CdTe Quantum Wells with Giant Rashba Splitting in Magnetic Fields up to 34 T. <i>Semiconductors</i> , 2018 , 52, 1386-1391	0.7	0
25	Terahertz plasmons in doped HgTe quantum well heterostructures: dispersion, losses, and amplification. <i>Applied Optics</i> , 2021 , 60, 8991-8998	1.7	0
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23	Variation of the emission frequency of a terahertz quantum cascade laser. <i>Technical Physics Letters</i> , 2016 , 42, 230-233	0.7	
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